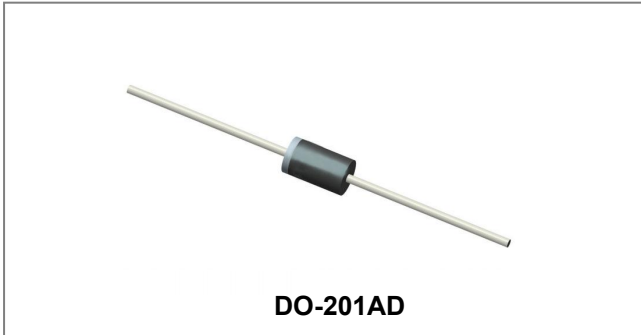


## 31DQ05/31DQ06 SCHOTTKY RECTIFIER



### Features

- Low profile, axial leaded outline
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	-	50(31DQ05) 60(31DQ06)	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 40^\circ\text{C}$ , rectangular wave form On PC board 9mm <sup>2</sup> island	3.3	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse, $T_C = 25^\circ\text{C}$	66	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 3A, Pulse, $T_J = 25^\circ\text{C}$ @ 6 A, Pulse, $T_J = 25^\circ\text{C}$	0.55 0.65	0.62 0.78	V
	$V_{F2}$	@ 3 A, Pulse, $T_J = 125^\circ\text{C}$ @ 6 A, Pulse, $T_J = 125^\circ\text{C}$	0.48 0.60	0.54 0.65	V
Reverse Current*	$I_{R1}$	@ $V_R = \text{Rated } V_R$ , Pulse, $T_J = 25^\circ\text{C}$	0.03	2	mA
	$I_{R2}$	@ $V_R = \text{Rated } V_R$ , Pulse, $T_J = 125^\circ\text{C}$	13	20	mA
Junction Capacitance	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	130	160	PF
Typical Series Inductance	$L_S$	Measured lead to lead 5 mm from package body	9.0	-	nH
Voltage Rate of Change	$dv/dt$	-	-	10,000	V/ $\mu\text{s}$

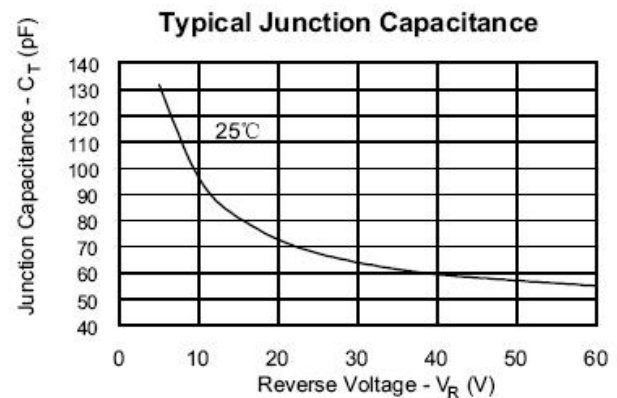
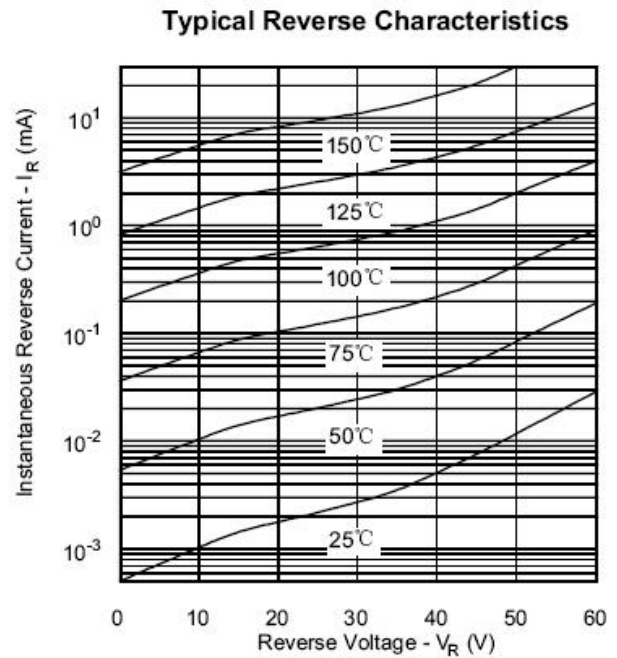
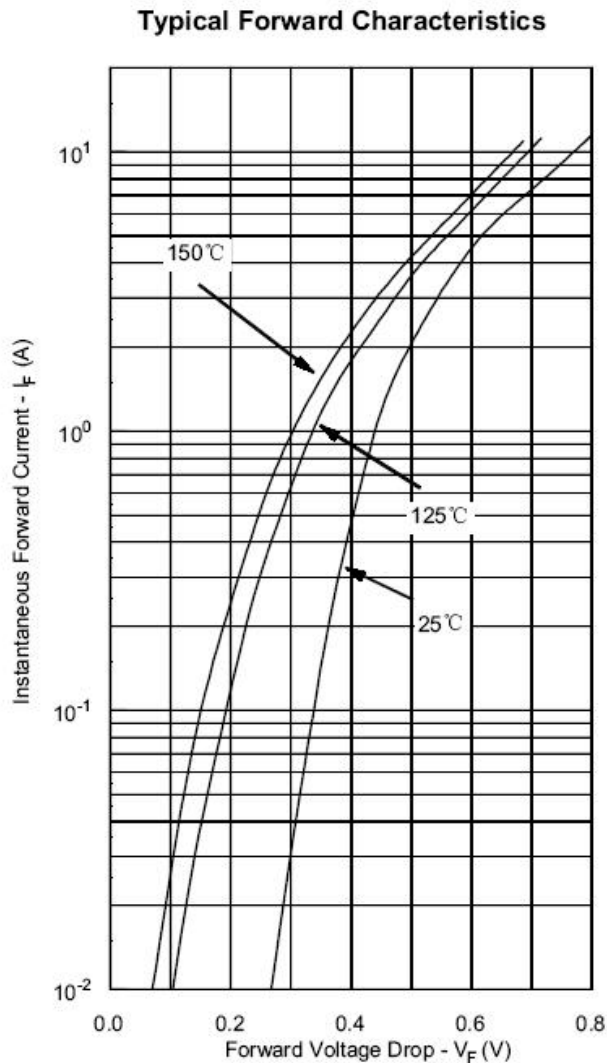
\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - [sales@smc-diodes.com](mailto:sales@smc-diodes.com) •

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-40 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-40 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta\text{JA}}$	-	80	$^{\circ}\text{C}/\text{W}$
Typical Thermal Resistance Junction to Lead	$R_{\theta\text{JL}}$	-	34	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	1.02	g

**Ratings and Characteristics Curves**



### Mechanical Dimensions DO-201AD



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	25.4	-	1.000	-
B	8.50	9.50	0.335	0.374
C	1.2	1.3	0.048	0.052
D	5.0	5.6	0.197	0.220

### Ordering Information

Device	Package	Shipping
31DQ05(6)	DO-201AD (Pb-Free)	1250pcs /Tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### Marking Diagram

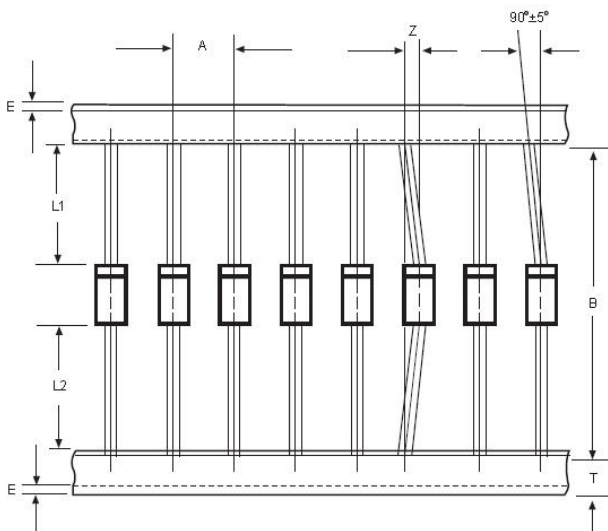


Where XXXXX is YYWWL

31DQ05 = Part Name  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

### Carrier Tape Specification DO-201AD



SYMBOL	Millimeters	
	Min.	Max.
A	9.50	10.50
B	50.9	53.9
Z	-	1.20
T	5.60	6.40
E	-	0.80
IL1-L2I	-	1.0

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